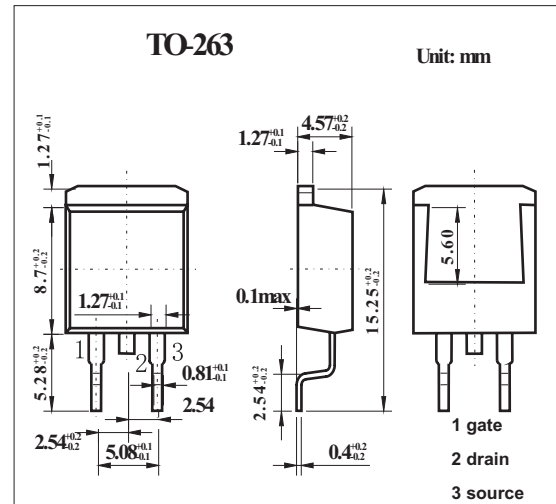
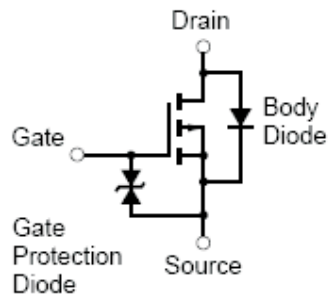


MOS Field Effect Transistors

2SJ605

■ Features

- Super low on-state resistance:
 $R_{DS(on)1} = 20 \text{ m}\Omega \text{ MAX. (} V_{GS} = -10 \text{ V, } I_D = -33 \text{ A)}$
 $R_{DS(on)2} = 31 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -33 \text{ A)}$
- Low input capacitance
 $C_{iss} = 4600 \text{ pF TYP. (} V_{DS} = -10 \text{ V, } V_{GS} = 0 \text{ A)}$
- Built-in gate protection diode



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to Source Voltage	V_{DSS}	-60	V
Gate to Source Voltage	V_{GSS}	± 20	V
Drain Current(DC)	I_D	± 65	A
Drain Current(pulse) *1	$I_{D(pulse)}$	± 200	A
Total Power Dissipation	P_T	1.5	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Single Avalanche Current *2	I_{AS}	-45	A
Single Avalanche Energy *2	E_{AS}	203	mJ

*1. $PW \leq 10\mu\text{s}$, D duty cycle $\leq 1\%$.

*2. Starting $T_{ch} = 25^\circ\text{C}$, $R_{\theta} = 25\Omega$, $V_{GS} = -20\text{V}$, $V_{DD} = -30\text{V}$

2SJ605

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain Cut-off Current	I_{DSS}	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$			-10	$\mu\text{ A}$
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			± 10	$\mu\text{ A}$
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$	-1.5	-2.0	-2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10\text{ V}, I_D = -33\text{ A}$	30	59		S
Drain to Source On-state Resistance	$R_{DS(on)1}$	$V_{GS} = -10\text{ V}, I_D = -33\text{ A}$		17	20	$\text{m}\Omega$
	$R_{DS(on)2}$	$V_{GS} = -4.0\text{ V}, I_D = -33\text{ A}$		22	31	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -10\text{ V}$		4600		pF
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$		820		pF
Feedback Capacitance	C_{rss}	$f = 1\text{ MHz}$		330		pF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -30\text{ V}, I_D = -33\text{ A}$		15		ns
Rise Time	t_r	$V_{GS} = -10\text{ V}$		14		ns
Turn-off Delay Time	$t_{d(off)}$	$R_G = 0\Omega$		100		ns
Fall Time	t_f			58		ns
Total Gate Charge	Q_g	$V_{DD} = -48\text{ V}$		87		nC
Gate-Source Charge	Q_{gs}	$V_{GS} = -10\text{ V}$		15		nC
Gate-Drain Charge	Q_{gd}	$I_D = -65\text{ A}$		22		nC
Diode Forward Voltage	$V_{F(S-D)}$	$I_F = 65\text{ A}, V_{GS} = 0\text{ V}$		1.0		V
Reverse Recovery Time	t_{rr}	$I_F = 65\text{ A}, V_{GS} = 0\text{ V}$		53		ns
Reverse Recovery Charge	Q_{rr}	$di/dt = 100\text{ A} / \mu\text{ s}$		110		nC